ESD11B5.0ST5G

Transient Voltage Suppressors

Micro−Packaged Diodes for ESD Protection

The ESD11B Series is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space comes at a premium.

Specification Features

- Low Capacitance 12 pF
- Low Clamping Voltage
- Small Body Outline Dimensions: 0.60 mm x 0.30 mm
- Low Body Height: 0.3 mm
- Stand−off Voltage: 5.0 V
- Low Leakage
- Response Time is < 1 ns
- IEC61000−4−2 Level 4 ESD Protection
- IEC61000−4−4 Level 4 EFT Protection
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Mechanical Characteristics

MOUNTING POSITION: Any
QUALIFIED MAX REFLOW TEMPERATURE: 260°C
Device Meets MSL 1 Requirements

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IEC 61000−4−2 (ESD) Contact Air		±15 ±15	kV
Total Power Dissipation on FR−5 Board (Note 1) @ T_A = 25°C	P_D	250	mW
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	400	°C/W
Junction and Storage Temperature Range	T_J, T_{stg}	−40 to +125	°C
Lead Solder Temperature − Maximum (10 Second Duration)	T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.
1. FR−5 = 1.0 x 0.75 x 0.62 in.

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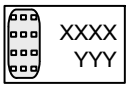
DSN2
CASE 152AA

MARKING DIAGRAM



XXXX = Specific Device Code
YYY = Year Code

ORDERING INFORMATION

Device	Package	Shipping†
ESD11B5.0ST5G	DSN2 (Pb−Free)	5000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

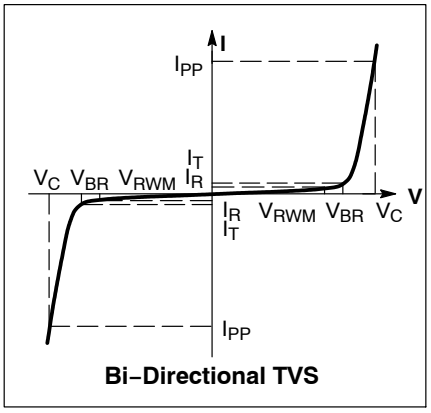
See Application Note AND8308/D for further description of survivability specs.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current

*See Application Note AND8308/D for detailed explanations of datasheet parameters.



Bi−Directional TVS

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Device	Device Marking	V_{RWM} (V)	I_R (μA) @ V_{RWM}	V_{BR} (V) @ I_T (Note 2)	I_T	C (pF)		V_C (V) @ I_{PP} = 1 A	V_C
		Max	Max	Min	mA	Typ	Max	Max (Note 3)	Per IEC61000−4−2 (Note 4)
ESD11B5.0ST5G	11B5	5.0	1.0	5.8	1.0	12	13.5	10	Figures 1 and 2 See Below

2. V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C.
3. Surge current waveforms per Figure 5.
4. For test procedure see Figures 3 and 4 and Application Note AND8307/D.

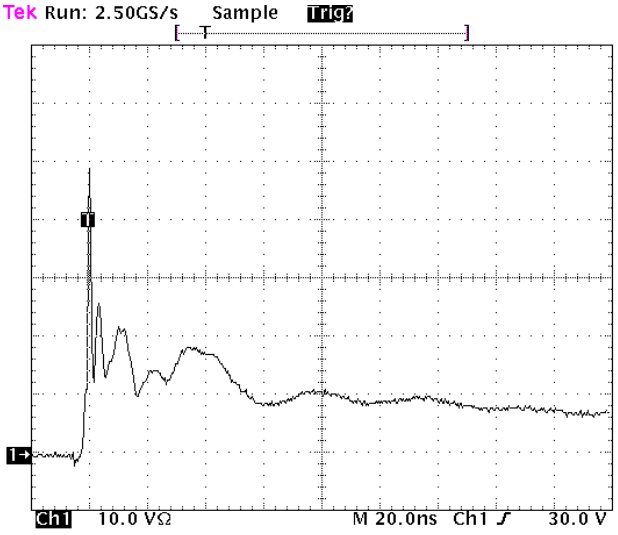


Figure 1. ESD Clamping Voltage Screenshot Positive 8 kV Contact per IEC61000−4−2

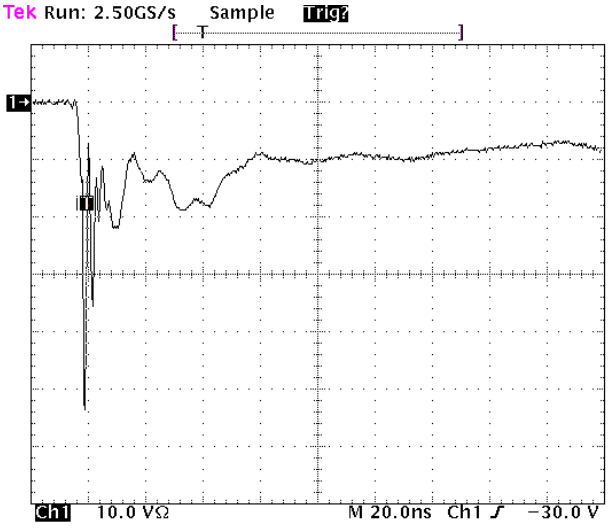


Figure 2. ESD Clamping Voltage Screenshot Negative 8 kV Contact per IEC61000−4−2

IEC 61000−4−2 Spec.

Level	Test Voltage (kV)	First Peak Current (A)	Current at 30 ns (A)	Current at 60 ns (A)
1	2	7.5	4	2
2	4	15	8	4
3	6	22.5	12	6
4	8	30	16	8

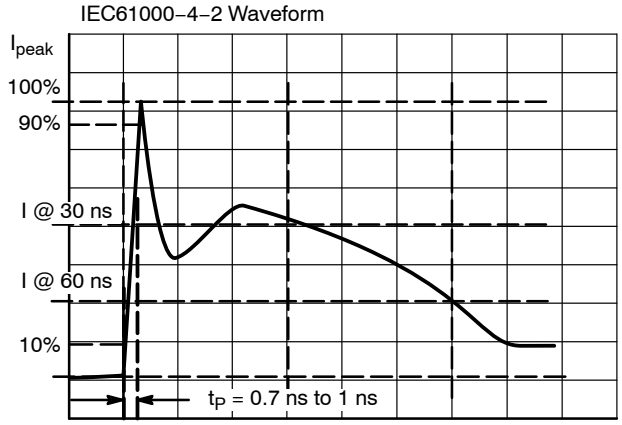


Figure 3. IEC61000−4−2 Spec

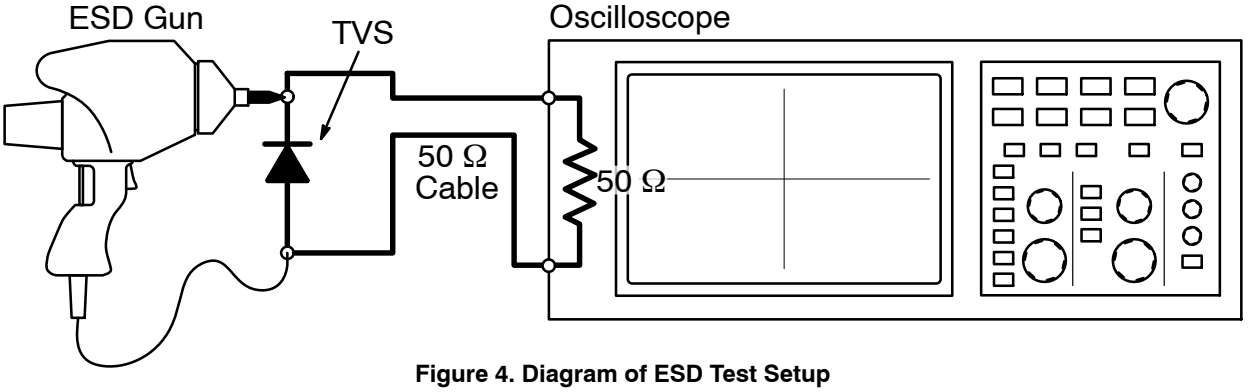


Figure 4. Diagram of ESD Test Setup

The following is taken from Application Note AND8308/D − Interpretation of Datasheet Parameters for ESD Devices.

ESD Voltage Clamping

For sensitive circuit elements it is important to limit the voltage that an IC will be exposed to during an ESD event to as low a voltage as possible. The ESD clamping voltage is the voltage drop across the ESD protection diode during an ESD event per the IEC61000−4−2 waveform. Since the IEC61000−4−2 was written as a pass/fail spec for larger systems such as cell phones or laptop computers it is not clearly defined in the spec how to specify a clamping voltage at the device level. ON Semiconductor has developed a way to examine the entire voltage waveform across the ESD protection diode over the time domain of an ESD pulse in the form of an oscilloscope screenshot, which can be found on the datasheets for all ESD protection diodes. For more information on how ON Semiconductor creates these screenshots and how to interpret them please refer to AND8307/D.

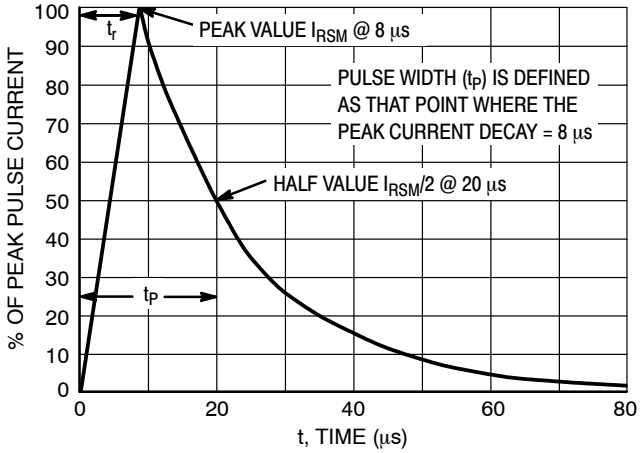
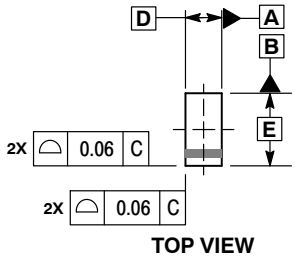


Figure 5. 8 X 20 μs Pulse Waveform

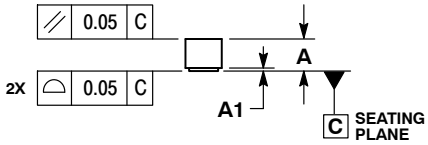
ESD11B5.0ST5G

PACKAGE DIMENSIONS

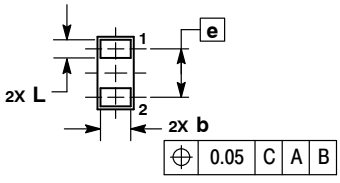
DSN2, 0.6x0.3, 0.4P, (0201)
CASE 152AA−01
ISSUE O



TOP VIEW



SIDE VIEW

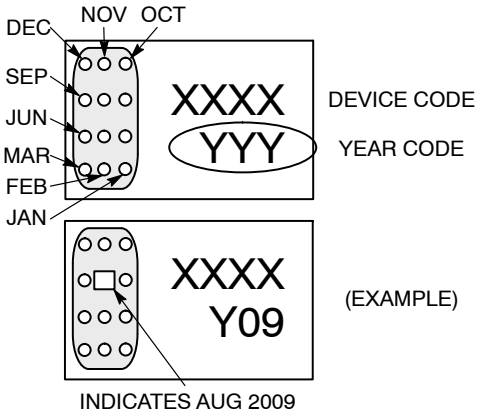


BOTTOM VIEW

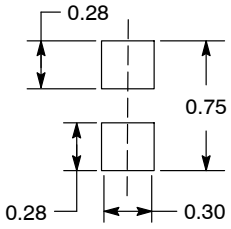
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.

	MILLIMETERS	
DIM	MIN	MAX
A	0.24	0.30
A1	0.00	0.01
b	0.22	0.28
D	0.30 BSC	
E	0.60 BSC	
e	0.40 BSC	
L	0.12	0.18

CATHODE BAND MONTH CODING



MOUNTING FOOTPRINT*



DIMENSIONS: MILLIMETERS

See Application Note AND8398/D for more mounting details

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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